

### **LISTING OF THE CLAIMS**

The following is a listing of claims pending in this case.

1.       **(Previously Presented)**       A method of fabricating a tunnel junction of a vertical cavity surface emitting laser (VCSEL), comprising:  
          locating a substrate in an MOCVD chamber;  
          setting a temperature of the MOCVD chamber between 500 °C and 650 °C; and  
          growing a tunnel junction including  $\text{GaAs}_{(1-x)}\text{Sb}_x$  on the substrate using an MOCVD process in which a source of Ga, a source of Sb, and a source of As are present.
2.       **(Original)**       The method according to claim 1, wherein x has a value corresponding to a ratio of As to Sb.
3.       **(Original)**       The method according to claim 2, wherein the value of x is 0.5.
4.       **(Original)**       The method according to claim 2, wherein the value of x is less than 0.5.
5.       **(Original)**       The method according to claim 1, wherein the source of Ga is TMGa or TEGa, and the source of Sb is TMSb.
6.       **(Original)**       The method according to claim 1, wherein the source of As is  $\text{AsH}_3$  or TBAs.
7.       **(Original)**       The method according to claim 1, further including carbon doping the  $\text{GaAs}_{(1-x)}\text{Sb}_x$  using  $\text{CCl}_4$  or  $\text{CBr}_4$ .
8.       **(Previously Presented)**       A tunnel junction having a p-doped  $\text{GaAs}_{(1-x)}\text{Sb}_x$  layer.
9.       **(Previously Presented)**       The tunnel junction according to claim 8, wherein the p-doped  $\text{GaAs}_{(1-x)}\text{Sb}_x$  layer is doped with carbon with a concentration greater than  $1 \times 10^{19} \text{ cm}^{-3}$ .

10. **(Previously Presented)** The tunnel junction according to claim 9, further including an n-doped layer of InP, AlInAs, AlInGaAs, or InGaAsP.

11. **(Previously Presented)** The tunnel junction according to claim 10, wherein the n-doped layer is doped with a concentration greater than  $5 \times 10^{19} \text{ cm}^{-3}$ , wherein the  $\text{GaAs}_{(1-x)}\text{Sb}_x$  layer is doped with a concentration greater than  $5 \times 10^{19} \text{ cm}^{-3}$ , and wherein the tunnel junction is less than about 10 nanometers thick.

12. **(Previously Presented)** The tunnel junction according to claim 10, wherein the n-doped layer is InP, and wherein x has a value of 0.5.

13. **(Original)** A vertical cavity surface emitting laser, comprising:  
an active region having a plurality of quantum wells, and  
a tunnel junction over said active region, wherein said tunnel junction includes a  $\text{GaAs}_{(1-x)}\text{Sb}_x$  layer.

14. **(Previously Presented)** The vertical cavity surface emitting laser according to claim 13, further including an n-type bottom spacer adjacent the active region, and an n-type bottom DBR adjacent the n-type bottom spacer.

15. **(Previously Presented)** The vertical cavity surface emitting laser according to claim 13, further including an n-type top spacer adjacent the tunnel junction and an n-type top DBR adjacent the n-type top spacer.

16. **(Previously Presented)** The vertical cavity surface emitting laser according to claim 13, wherein the  $\text{GaAs}_{(1-x)}\text{Sb}_x$  layer is grown by MOCVD.

17. **(Previously Presented)** The vertical cavity surface emitting laser according to claim 13, wherein the  $\text{GaAs}_{(1-x)}\text{Sb}_x$  layer is doped with carbon with a concentration greater than  $5 \times 10^{19} \text{ cm}^{-3}$ .

18.     **(Previously Presented)**         The vertical cavity surface emitting laser according to claim 13, wherein said active region includes InGaAsP or AlInGaAs.

19.     **(Previously Presented)**         The vertical cavity surface emitting laser according to claim 18, wherein said tunnel junction includes an n-type InP layer.

20.     **(Previously Presented)**         The vertical cavity surface emitting laser according to claim 13, wherein x is 0.5.

21.     **(Previously Presented)**         The vertical cavity surface emitting laser according to claim 13, wherein the tunnel junction has a thickness of less than about 10 nm.